# PBSS4041NX

## 60 V, 6.2 A NPN low VCEsat (BISS) transistor

11 December 2012

**Product data sheet** 

## 1. Technical summary

NPN low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a medium power and flat lead SOT89 (SC-62) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS4041PX.

### 2. Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- High energy efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

## 3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	60	V
I <sub>C</sub>	collector current		-	-	6.2	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	15	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 4 A; $I_B$ = 400 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	25	35	mΩ



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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		2
2	С	collector		3——
3	В	base	3 2 1 SOT89	1 sym042

## 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS4041NX	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89			

## 7. Marking

Table 4. Marking codes

Type number	Marking code
	[1]
PBSS4041NX	%6F

<sup>[1] % =</sup> placeholder for manufacturing site code

## 8. Limiting values

Table 5. Limiting values

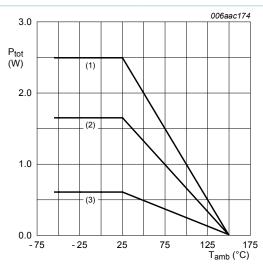
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	60	V
$V_{CEO}$	collector-emitter voltage	open base		-	60	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	5	V
I <sub>C</sub>	collector current			-	6.2	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	15	Α
I <sub>B</sub>	base current			-	1	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	600	mW
			[2]	-	1650	mW
			[3]	-	2500	mW
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Symbol	Parameter	Conditions	Min	Max	Unit
T <sub>j</sub>	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	150	°C
T <sub>stg</sub>	storage temperature		-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ang ay	thermal resistance	in free air	[1]	-	-	210	K/W
	from junction to ambient		[2]	-	-	75	K/W
	ambient		[3]	-	-	50	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

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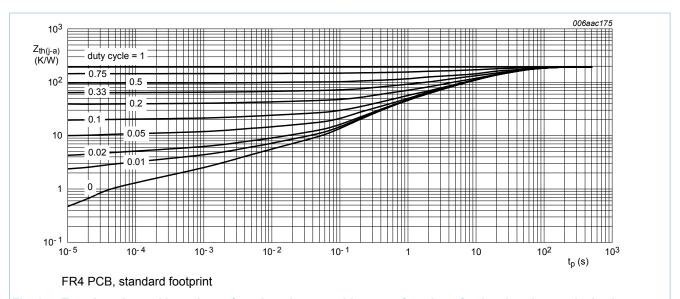


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

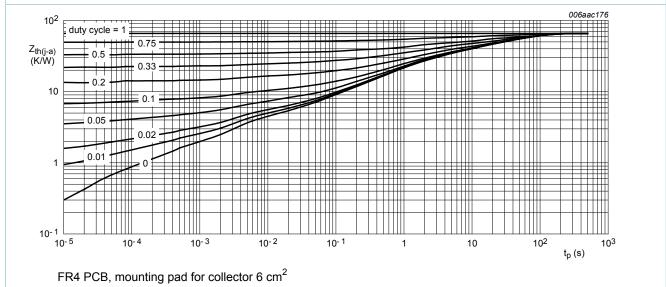
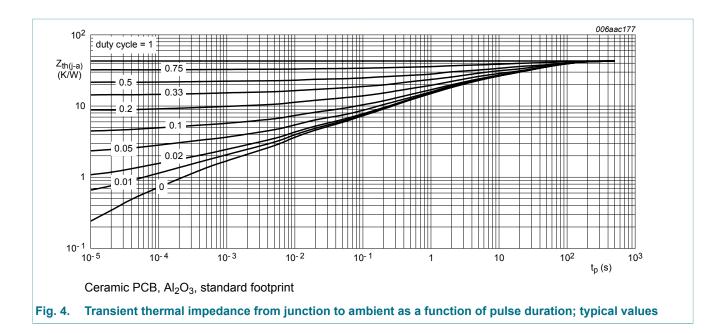


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

**Product data sheet** 

### 60 V, 6.2 A NPN low VCEsat (BISS) transistor



## 10. Characteristics

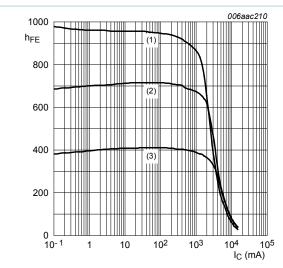
Table 7. Characteristics

Symbol	Parameter	Conditions	Mi	n '	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = 60 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-		-	100	nA
	current	$V_{CB} = 60 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-		-	50	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = 48 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-		-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-		-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 2 V; $I_{C}$ = 500 mA; pulsed; $t_{p}$ ≤ 300 µs; $\delta$ ≤ 0.02 ; $T_{amb}$ = 25 °C	30	00	500	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 1 A; pulsed; $t_{p} \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	30	00	500	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 2 A; pulsed; $t_{p} \le 300 \ \mu s$ ; $\overline{\delta} \le 0.02$ ; $T_{amb}$ = 25 °C	25	50	450	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 4 A; pulsed; $t_{p}$ ≤ 300 $\mu$ s; $\delta$ ≤ 0.02 ; $T_{amb}$ = 25 °C	15	50	250	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 6 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02 ; $T_{amb}$ = 25 °C	75	5	120	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = 1 A; $I_{B}$ = 50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \bar{o} \le 0.02 \ ; T_{amb}$ = 25 °C	-		35	50	mV
		$I_C$ = 1 A; $I_B$ = 10 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	-		50	80	mV

### 60 V, 6.2 A NPN low VCEsat (BISS) transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$I_{C}$ = 2 A; $I_{B}$ = 40 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	-	95	145	mV
		$I_C$ = 4 A; $I_B$ = 200 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	110	150	mV
		$I_{C}$ = 4 A; $I_{B}$ = 40 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	240	320	mV
		$I_{C}$ = 6 A; $I_{B}$ = 300 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02 ; $T_{amb}$ = 25 °C	-	150	210	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = 4 A; $I_{B}$ = 400 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	25	35	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C}$ = 1 A; $I_{B}$ = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	0.82	0.9	V
		$I_{C}$ = 4 A; $I_{B}$ = 400 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	0.92	1.05	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = 2 V; $I_{C}$ = 2 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	0.75	0.85	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = 12.5 V; I <sub>C</sub> = 1 A; I <sub>Bon</sub> = 0.05 A;	-	35	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -0.05 A; T <sub>amb</sub> = 25 °C	-	65	-	ns
t <sub>on</sub>	turn-on time		-	100	-	ns
t <sub>s</sub>	storage time		-	1050	-	ns
t <sub>f</sub>	fall time		-	220	-	ns
t <sub>off</sub>	turn-off time		-	1270	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	130	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	35	-	pF

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$$V_{CE} = 2 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55$$
 °C

Fig. 5. DC current gain as a function of collector current; typical values

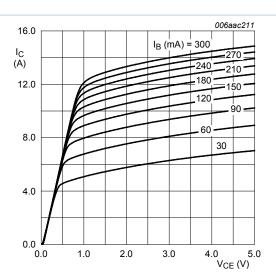
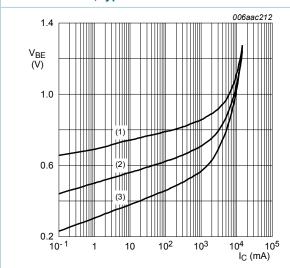


Fig. 6. Collector current as a function of collectoremitter voltage; typical values



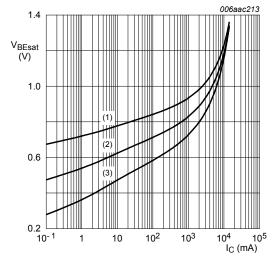
$$V_{CE} = 2 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = 100 °C$$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

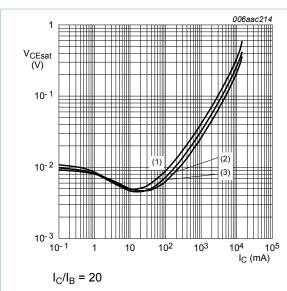
(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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(1) 
$$T_{amb}$$
 = 100 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55$$
 °C

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

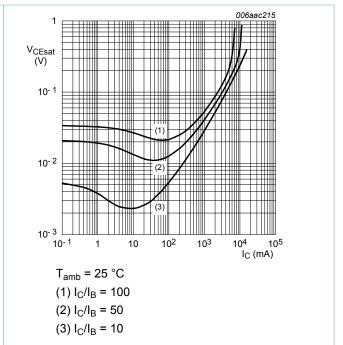
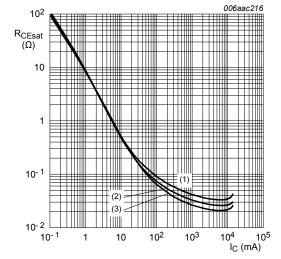


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values



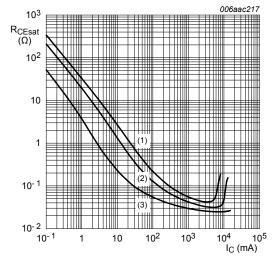
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$I_C/I_B = 100$$

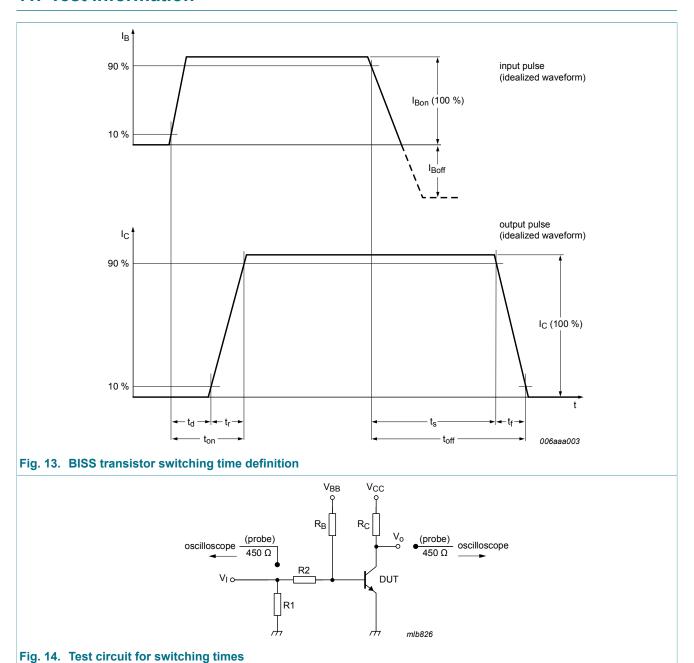
(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

60 V, 6.2 A NPN low VCEsat (BISS) transistor

## 11. Test information

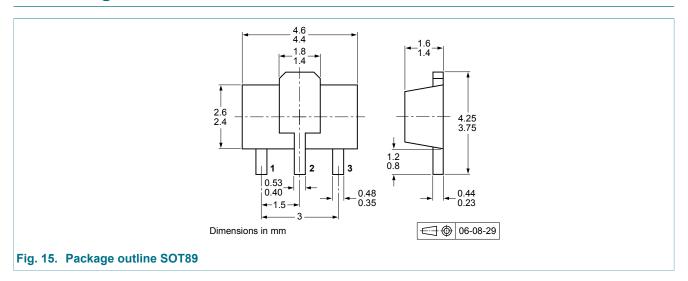


## 11.1 Quality information

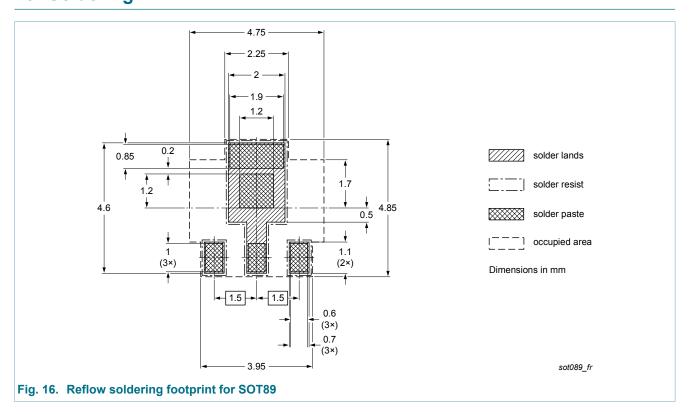
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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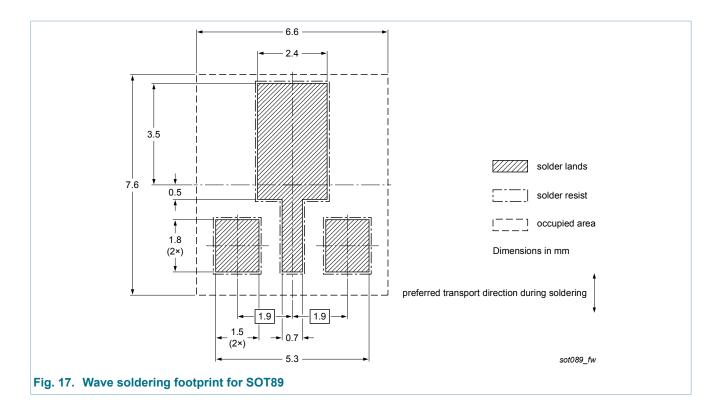
## 12. Package outline



## 13. Soldering



### 60 V, 6.2 A NPN low VCEsat (BISS) transistor



## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4041NX v.3	20121211	Product data sheet	-	PBSS4041NX v.2
Modifications:	Editorial update			,
PBSS4041NX v.2	20121010	Product data sheet	-	PBSS4041NX v.1
PBSS4041NX v.1	20100401	Product data sheet	-	-

#### 60 V, 6.2 A NPN low VCEsat (BISS) transistor

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